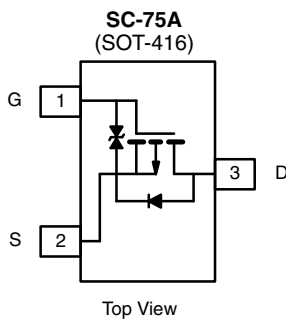


## P-Channel 60 V (D-S) MOSFET

### PRODUCT SUMMARY

$V_{DS(min.)}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$V_{GS(th)}$ (V)	$I_D$ (mA)
- 60	4.0 at $V_{GS} = - 10$ V	- 1 to 3.0	- 190



Marking Code: F

**Ordering Information:** Si1021R-T1-GE3 (Lead (Pb)-free and Halogen-free)

### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFETs
- High-Side Switching
- Low On-Resistance: 4  $\Omega$
- Low Threshold: - 2 V (typ.)
- Fast Switching Speed: 20 ns (typ.)
- Low Input Capacitance: 20 pF (typ.)
- Miniature Package
- ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC


**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**

### APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Power Supply Converter Circuits
- Solid-State Relays

### BENEFITS

- Ease in Driving Switches
- Low Offset Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Easily Driven without Buffer
- Small Board Area

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	- 60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	- 190
		$T_A = 85$ °C	- 135
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	- 650	mA
Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	250
		$T_A = 85$ °C	130
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	500	°C/W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

Notes:

a. Surface mounted on FR4 board.

b. Pulse width limited by maximum junction temperature.

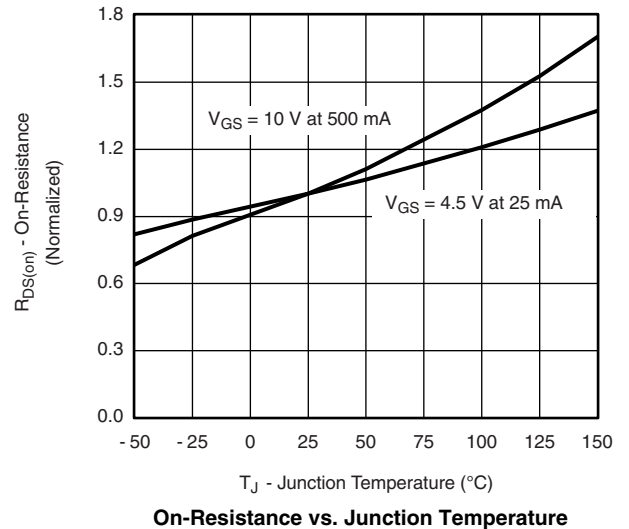
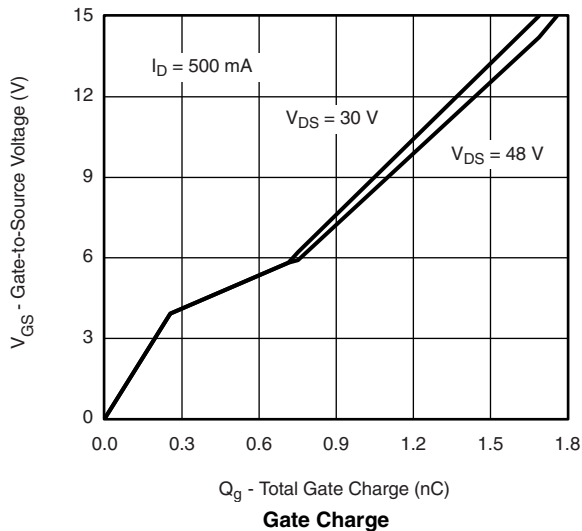
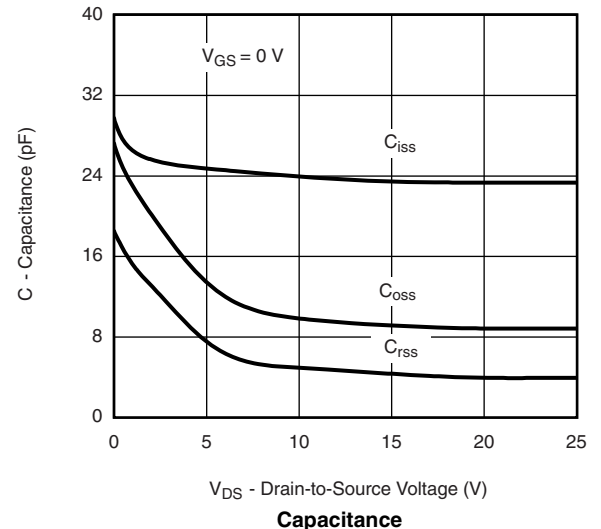
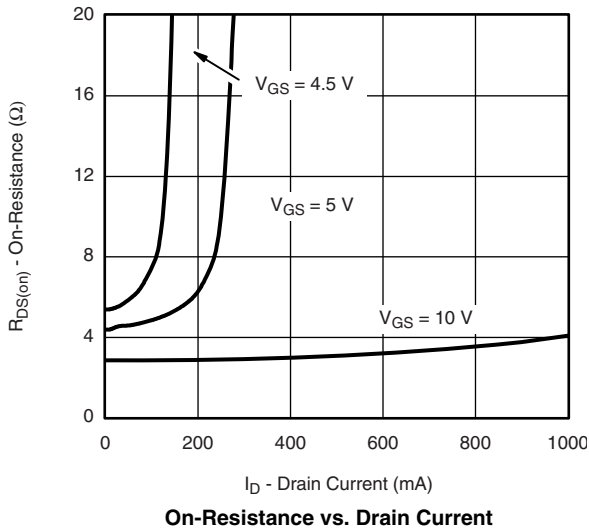
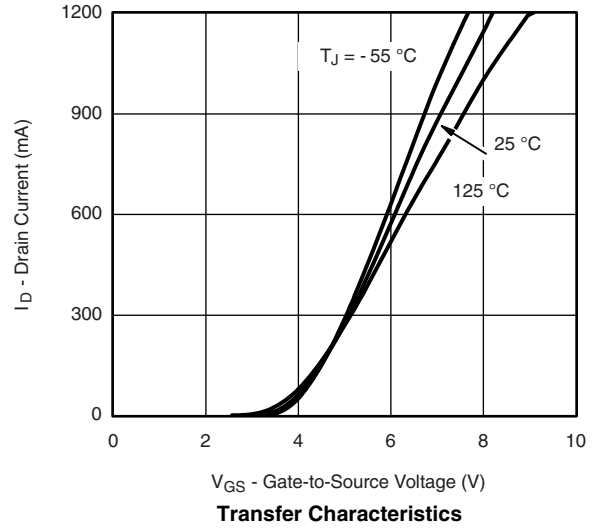
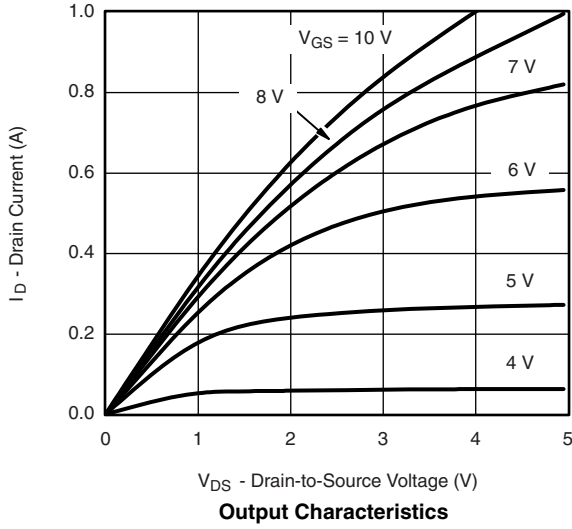
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = -10\text{ }\mu\text{A}$	- 60			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -0.25\text{ mA}$	- 1		- 3.0	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 10$	$\mu\text{A}$  $\text{nA}$
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}$			$\pm 200$	
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}, T_J = 85\text{ }^\circ\text{C}$			$\pm 500$	
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$			$\pm 100$	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -50\text{ V}, V_{GS} = 0\text{ V}$			- 25	
		$V_{DS} = -50\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			- 250	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}$	- 50			mA
		$V_{DS} = -10\text{ V}, V_{GS} = -10\text{ V}$	- 600			
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -25\text{ mA}$			8	$\Omega$
		$V_{GS} = -10\text{ V}, I_D = -500\text{ mA}$			4	
		$V_{GS} = -10\text{ V}, I_D = -500\text{ mA}, T_J = 125\text{ }^\circ\text{C}$			6	
Forward Transconductance	$g_{fs}$	$V_{DS} = -10\text{ V}, I_D = -100\text{ mA}$	80			mS
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$V_{DS} = -200\text{ mA}, V_{GS} = 0\text{ V}$	80			V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS} = -30\text{ V}, V_{GS} = -15\text{ V}, I_D \cong -500\text{ mA}$		1.7		nC
Gate-Source Charge	$Q_{gs}$			0.26		
Gate-Drain Charge	$Q_{gd}$			0.46		
Input Capacitance	$C_{iss}$	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		23		pF
Output Capacitance	$C_{oss}$			10		
Reverse Transfer Capacitance	$C_{rss}$			5		
<b>Switching<sup>b</sup></b>						
Turn-On Time	$t_{ON}$	$V_{DD} = -25\text{ V}, R_L = 150\text{ }\Omega,$ $I_D \cong -200\text{ mA}, V_{GEN} = -10\text{ V}, R_g = 10\text{ }\Omega$		20		ns
Turn-Off Time	$t_{OFF}$			35		

Notes:

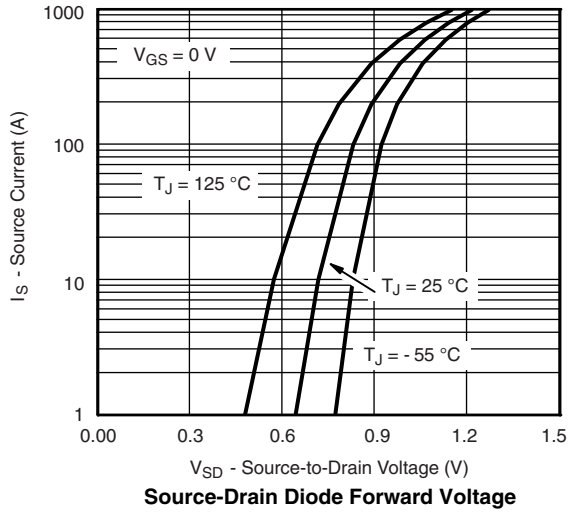
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

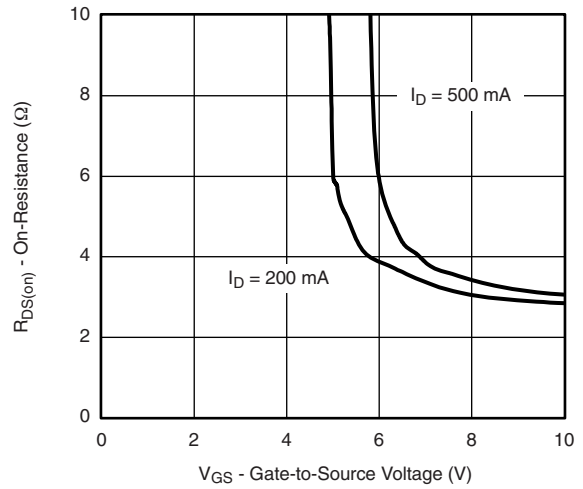
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



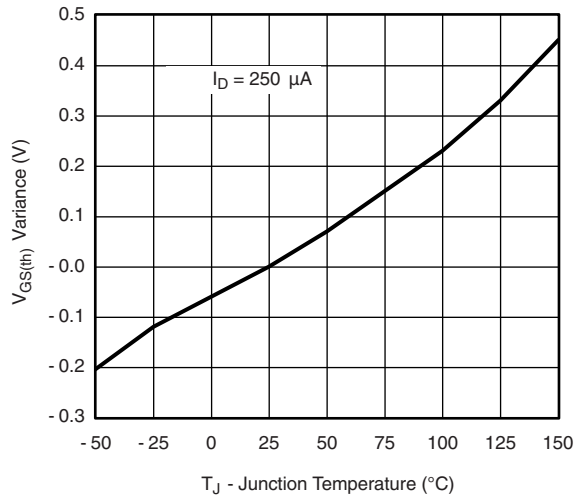
### TYPICAL CHARACTERISTICS ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



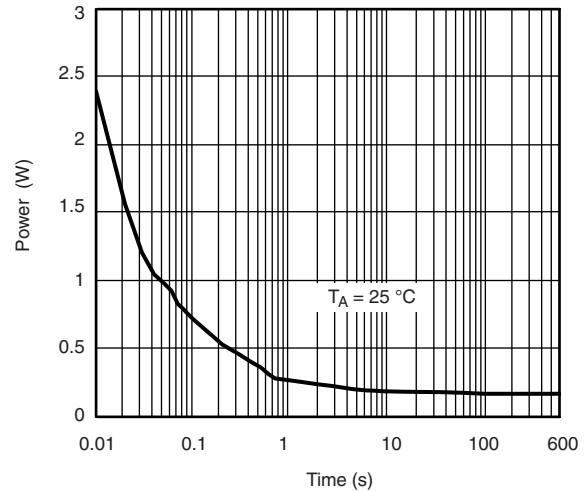
Source-Drain Diode Forward Voltage



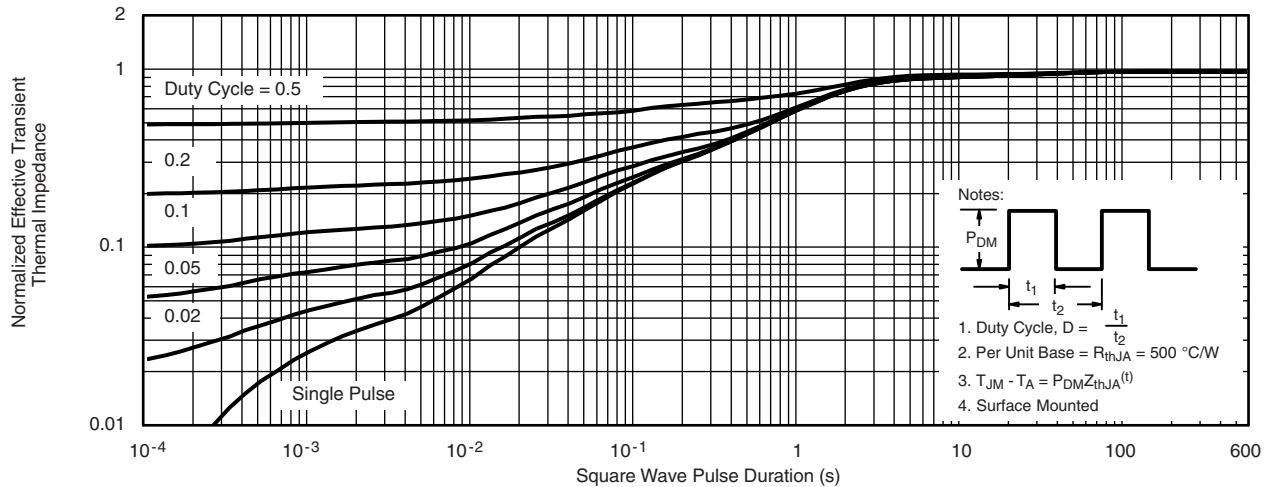
On-Resistance vs. Gate-Source Voltage



Threshold Voltage Variance Over Temperature



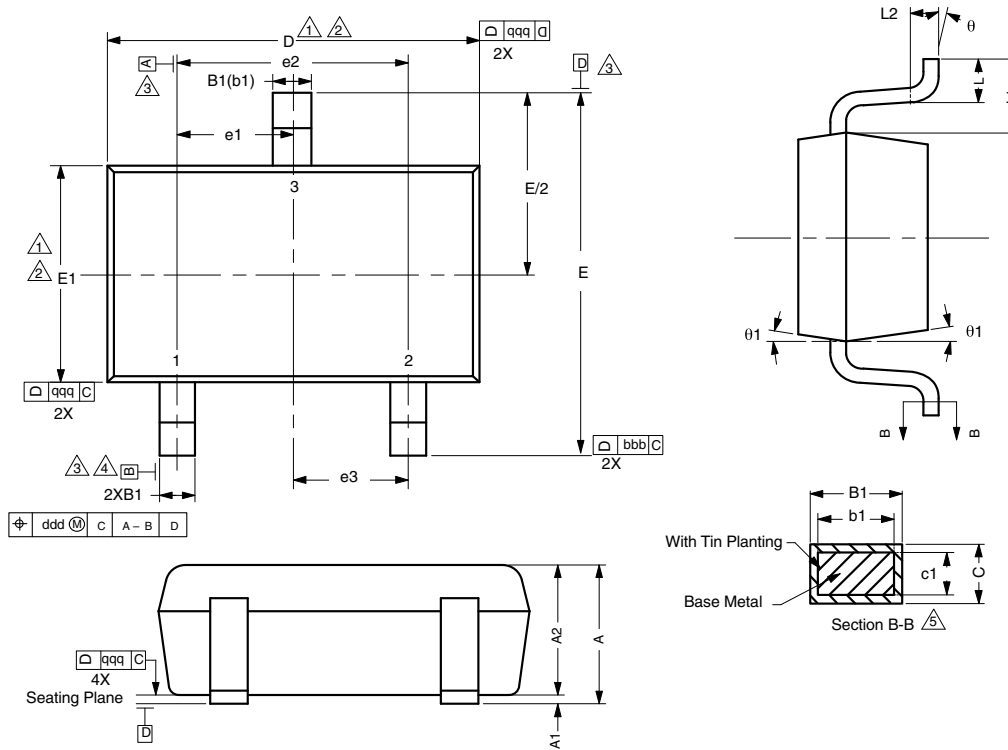
Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?71410](http://www.vishay.com/ppg?71410).

### SC-75A: 3 Leads



DWG: 5868

**Notes**

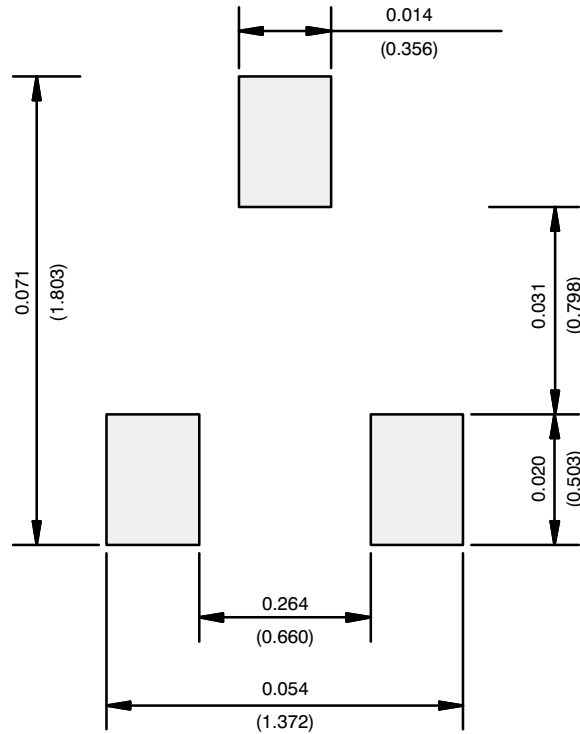
Dimensions in millimeters will govern.

- 1. Dimension D does not include mold flash, protrusions or gate burrs. Mold flash protrusions or gate burrs shall not exceed 0.10 mm per end. Dimension E1 does not include Interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.10 mm per side.
- 2. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
- 3. Datums A, B and D to be determined 0.10 mm from the lead tip.
- 4. Terminal positions are shown for reference only.
- 5. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIMENSIONS	TOLERANCES
aaa	0.10
bbb	0.10
ccc	0.10
ddd	0.10

DIM.	MILLIMETERS			NOTE
	MIN.	NOM.	MAX.	
A	-	-	0.80	
A1	0.00	-	0.10	
A2	0.65	0.70	0.80	
B1	0.19	-	0.24	5
b1	0.17	-	0.21	
c	0.13	-	0.15	5
c1	0.10	-	0.12	5
D	1.48	1.575	1.68	1, 2
E	1.50	1.60	1.70	
E1	0.66	0.76	0.86	1, 2
e1	0.50 BSC			
e2	1.00 BSC			
e3	0.50 BSC			
L	0.15	0.205	0.30	
L1	0.40 ref.			
L2	0.15 BSC			
q	0°	-	8°	
q1	4°	-	10°	

## RECOMMENDED MINIMUM PADS FOR SC-75A: 3-Lead



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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